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Team Nexperia

NPN 800 mA, 40 V BISS RETs; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

Rev. 01 — 27 February 2007

**Product data sheet** 

### 1. Product profile

### 1.1 General description

800 mA NPN low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) Resistor-Equipped Transistors (RET) family in small plastic packages.

#### Table 1. Product overview

Type number	Package	Package					
	NXP	JEITA	JEDEC				
PBRN123YK	SOT346	SC-59A	TO-236				
PBRN123YS <sup>[1]</sup>	SOT54	SC-43A	TO-92				
PBRN123YT	SOT23	-	TO-236AB				

V<sub>CEsat</sub>

Switching loads

[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

### 1.2 Features

- 800 mA output current capability
- High current gain h<sub>FE</sub>
- Built-in bias resistors
- Simplifies circuit design

### **1.3 Applications**

- Digital application in automotive and industrial segments
- Medium current peripheral driver

### 1.4 Quick reference data

#### Table 2. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
$V_{\text{CEO}}$	collector-emitter voltage	open base		-	-	40	V
lo	output current		<u>[1]</u>				
	PBRN123YK, PBRN123YT	-		-	-	600	mA
	PBRN123YS			-	-	800	mA



Low collector-emitter saturation voltage

Reduces component count

Reduces pick and place costs

■ ±10 % resistor ratio tolerance

## **PBRN123Y series**

### NPN 800 mA, 40 V BISS RETs; R1 = 2.2 kΩ, R2 = 10 kΩ

Table 2.	Quick reference data continued					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I <sub>ORM</sub>	repetitive peak output current					
	PBRN123YK, PBRN123YT	$t_p \le 1 ms; \delta \le 0.33$	-	-	800	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		4.1	4.55	5	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

## 2. Pinning information

Pin	Description	Simplified outline	Symbol
SOT54			
1	input (base)		
2	output (collector)		2
3	GND (emitter)	001aab347	1 R1 R2 006aaa145
SOT54A			
1	input (base)		
2	output (collector)		2
3	GND (emitter)	1 2 001aab348	1 R2 006aaa145
SOT54 va	riant		
1	input (base)		
2	output (collector)	THE STREET	
3	GND (emitter)	001aab447	1 - R1 R2 006aaa145
SOT23; S	OT346		
1	input (base)		
2	GND (emitter)	3	3
3	output (collector)	12006aaa144	1 R2 R2 sym007

PBRN123Y\_SER\_1
Product data sheet

NPN 800 mA, 40 V BISS RETs; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

### 3. Ordering information

Table 4.         Ordering information						
Type number	Package	Package				
	Name	Description	Version			
PBRN123YK	SC-59A	plastic surface-mounted package; 3 leads	SOT346			
PBRN123YS <sup>[1]</sup>	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54			
PBRN123YT	-	plastic surface-mounted package; 3 leads	SOT23			

[1] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

### 4. Marking

Marking code <sup>[1]</sup>
G7
N123YS
*7P

- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

## 5. Limiting values

#### Table 6.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	40	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	40	V
$V_{\text{EBO}}$	emitter-base voltage	open collector	-	5	V
VI	input voltage				
	positive		-	+22	V
	negative		-	-5	V
lo	output current				
	PBRN123YK, PBRN123YT		<u>[1]</u> _	600	mA
			[2][3]	700	mA
	PBRN123YS		<u>[1]</u> _	800	mA
I <sub>ORM</sub>	repetitive peak output current				
	PBRN123YK, PBRN123YT	$t_p \leq 1 ms;  \delta \leq 0.33$	-	800	mA

#### NPN 800 mA, 40 V BISS RETs; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$

#### Table 6. Limiting values ...continued

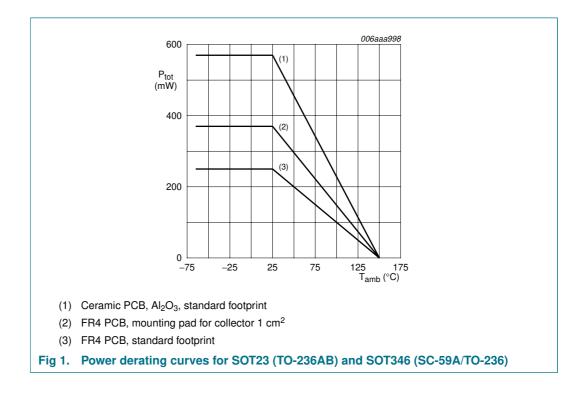
In accordance with the Absolute Maximum Rating System (IEC 60134).

		0,0	/		
Symbol	Parameter	Conditions	Min	Мах	Unit
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PBRN123YK, PBRN123YT		<u>[1]</u> _	250	mW
			[2] _	370	mW
			[3] _	570	mW
	PBRN123YS		<u>[1]</u> -	700	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

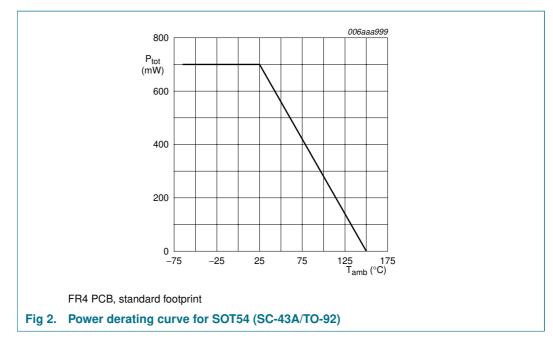
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.



NPN 800 mA, 40 V BISS RETs; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 



## 6. Thermal characteristics

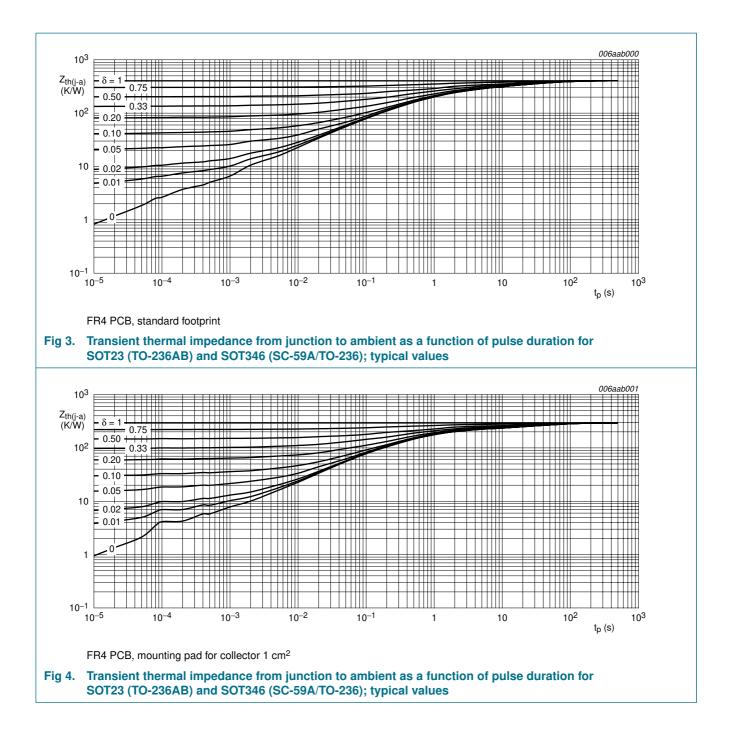
Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	PBRN123YK, PBRN123YT		<u>[1]</u> _	-	500	K/W
			[2] _	-	338	K/W
			[3]	-	219	K/W
	PBRN123YS		<u>[1]</u> _	-	179	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point					
	PBRN123YK, PBRN123YT		-	-	105	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

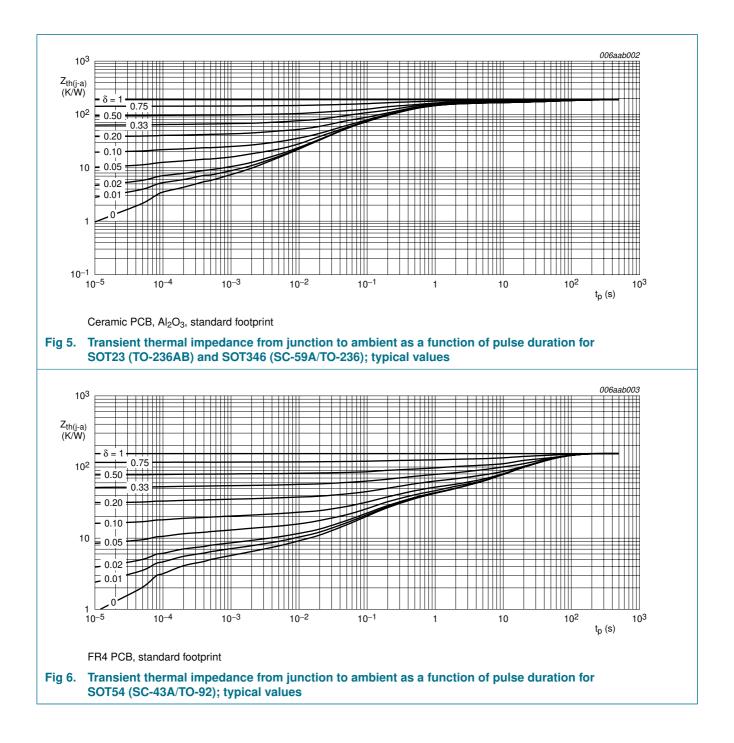
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

## **PBRN123Y series**



## **PBRN123Y series**



NPN 800 mA, 40 V BISS RETs; R1 = 2.2 kΩ, R2 = 10 kΩ

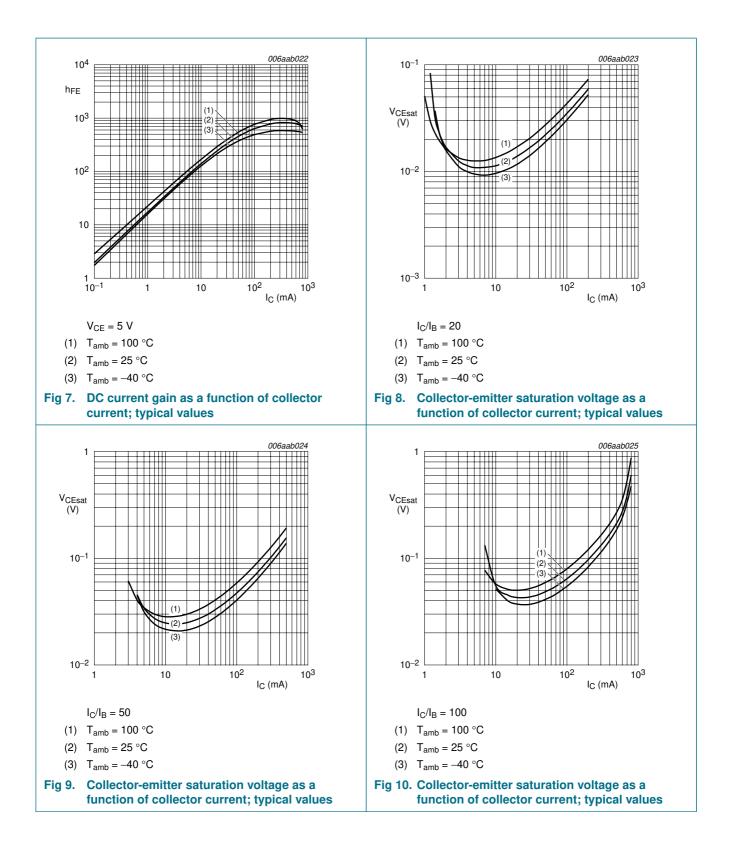
## 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A		-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A		-	-	0.5	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 V;$ $I_{C} = 0 A$		-	-	0.65	mA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 50 mA		300	450	-	
		$V_{CE} = 5 V;$ $I_C = 300 mA$	<u>[1]</u>	500	750	-	
		$V_{CE} = 5 V;$ $I_C = 600 mA$	[1]	500	720	-	
		V <sub>CE</sub> = 5 V; I <sub>C</sub> = 800 mA	[1]	450	650	-	
V <sub>CEsat</sub> collector-emitter saturation voltage		I <sub>C</sub> = 50 mA; I <sub>B</sub> = 2.5 mA		-	25	35	mV
		I <sub>C</sub> = 200 mA; I <sub>B</sub> = 10 mA		-	60	85	mV
		I <sub>C</sub> = 500 mA; I <sub>B</sub> = 10 mA	<u>[1]</u>	-	160	220	mV
		I <sub>C</sub> = 600 mA; I <sub>B</sub> = 6 mA	<u>[1]</u>	-	270	550	mV
		I <sub>C</sub> = 800 mA; I <sub>B</sub> = 8 mA	<u>[1]</u>	-	0.56	1.15	V
V <sub>I(off)</sub>	off-state input voltage	$V_{CE} = 5 V;$ $I_C = 100 \mu A$		0.4	0.6	1	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = 0.3 \text{ V};$ $I_{C} = 20 \text{ mA}$		0.5	0.8	1.4	V
R1	bias resistor 1 (input)			1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio			4.1	4.55	5	
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = i <sub>e</sub> = 0 A; f = 1 MHz		-	7	-	pF

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .

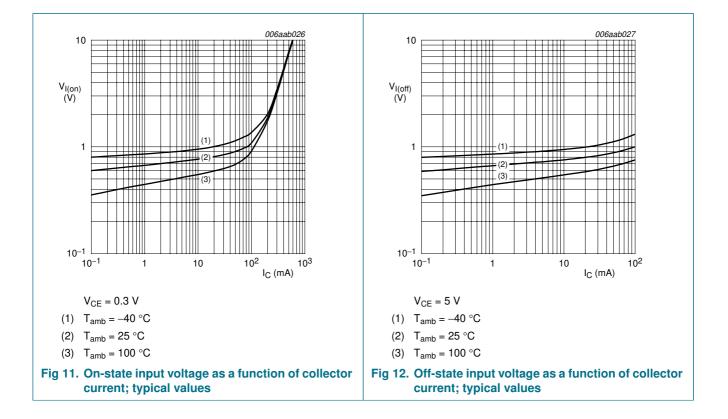
## **PBRN123Y series**

#### NPN 800 mA, 40 V BISS RETs; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$



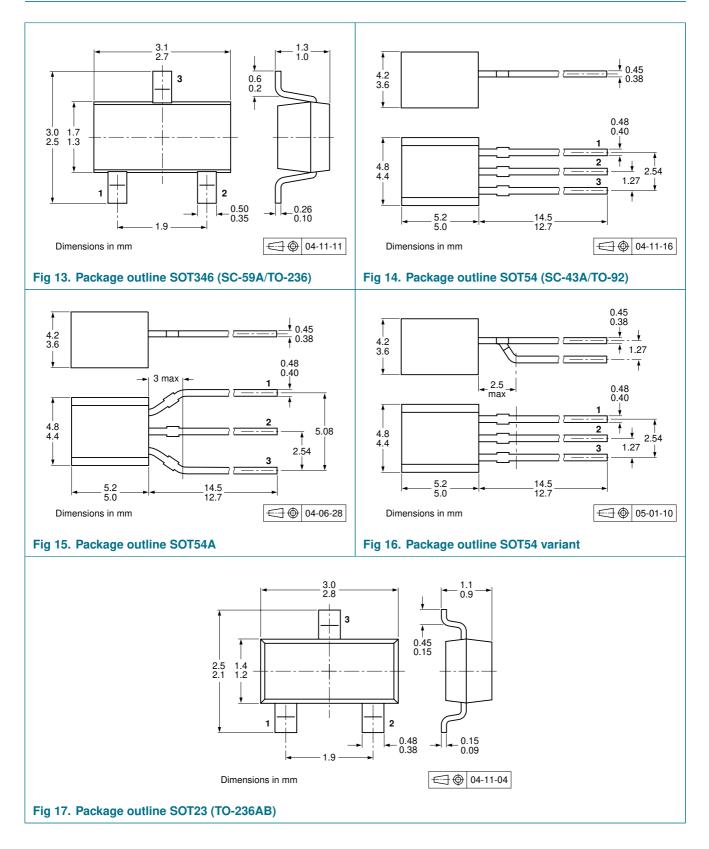
PBRN123Y SER 1

## **PBRN123Y series**



NPN 800 mA, 40 V BISS RETs; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

### 8. Package outline



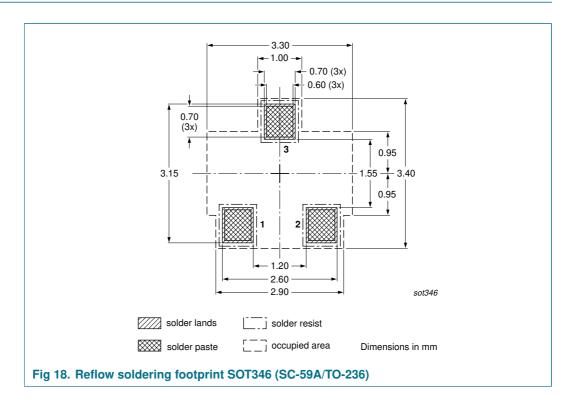
NPN 800 mA, 40 V BISS RETs; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

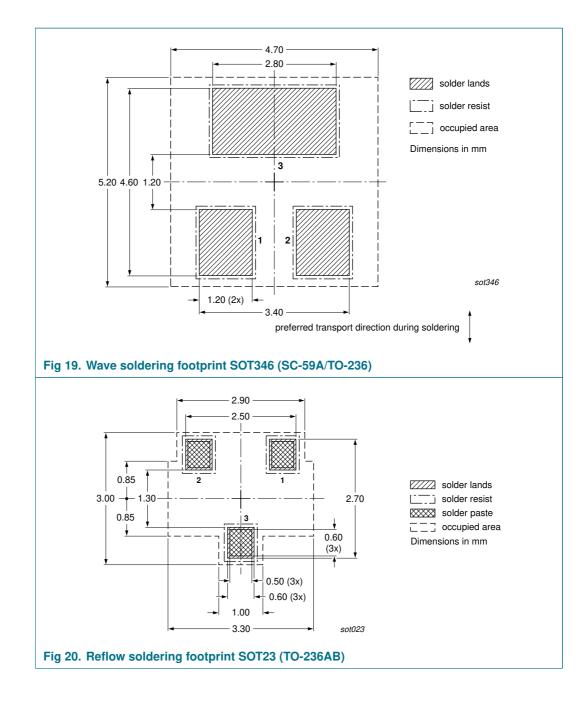
### 9. Packing information

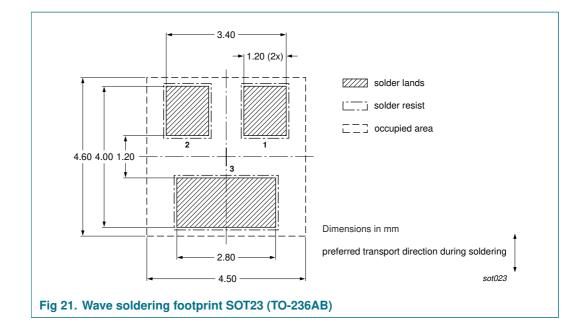
Table 9.         Packing methods           The indicated -xxx are the last three digits of the 12NC ordering code.[1]						
Package	Description	Packin	g quant	ity		
		3000	5000	10000		
SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135		
SOT54	bulk, straight leads	-	-412	-		
SOT54A	tape and reel, wide pitch	-	-	-116		
	tape ammopack, wide pitch	-	-	-126		
SOT54 variant	bulk, delta pinning	-	-112	-		
SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235		
	XXX are the last the Package SOT346 SOT54 SOT54A SOT54 variant	XXX are the last three digits of the 12NC ordering code.[1]PackageDescriptionSOT3464 mm pitch, 8 mm tape and reelSOT54bulk, straight leadsSOT54Atape and reel, wide pitchtape ammopack, wide pitchSOT54 variantSOT54 variantbulk, delta pinning	xxx are the last three digits of the 12NC ordering code.[1]         Package       Description       Packin 3000         SOT346       4 mm pitch, 8 mm tape and reel       -115         SOT54       bulk, straight leads       -         SOT54A       tape and reel, wide pitch       -         SOT54 variant       bulk, delta pinning       -	xxx are the last three digits of the 12NC ordering code.[1]PackageDescriptionPacking quant 3000SOT3464 mm pitch, 8 mm tape and reel-115-SOT54bulk, straight leads412SOT54Atape and reel, wide pitchSOT54 variantbulk, delta pinning112		

[1] For further information and the availability of packing methods, see Section 13.

## 10. Soldering







NPN 800 mA, 40 V BISS RETs; R1 = 2.2 kΩ, R2 = 10 kΩ

## **11. Revision history**

Table 10. Revision hist	10. Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
PBRN123Y_SER_1	20070227	Product data sheet	-	-				

NPN 800 mA, 40 V BISS RETs; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

## 12. Legal information

### 12.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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## **PBRN123Y series**

NPN 800 mA, 40 V BISS RETs; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

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**PHILIPS** 

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